



Session Title:	[TuB2] Power Device II
Session Date:	November 12 (Tue.), 2024
Session Time:	14:55-16:35
Session Room:	Room B (Grand Ballroom 1, 2F, Paradise Hotel Busan)
Session Chair:	Prof. Ogyun Seok (Pusan Nat'l Univ., Korea)

[TuB2-1] [Invited]

14:55-15:25

High Quality SiC Single Crystals Obtained with Modification of Crucible Structure and Process Condition in PVT Growth

Won Jae Lee (Dong-Eui Univ., Korea), Jung Gyu Kim, and Kap Ryeol Ku (Senic, Korea)

[TuB2-2] [Invited]

15:25-15:50

Investigation of β -Ga₂O₃ Based Hetero-Junction Barrier Schottky Diode

Yusup Jung, TaiYoung Kang, and SinSu Kyoung (PowerCubeSemi Inc., Korea)

[TuB2-3] [Invited]

15:50-16:15

Flat Wire Inductor for Wide Bandgap Power Devices' Characterization

Hyemin Kang (KENTECH, Korea)

[TuB2-4]

16:15-16:35

Study for the 4H-SiC FIN-Channel MOSFET with Additional Channels with Improved the Electrical Characteristics

Min Seok Jang, Hee Jin Kim (Pusan Nat'l Univ., Korea), Sung Mo Koo (Nat'l Inst. for Nanomaterials Tech., Korea), Yu Jeong Lee (Kyungpook Nat'l Univ., Korea), and Ho Jun Lee (Pusan Nat'l Univ., Korea)